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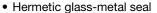
Vishay Semiconductors

### **Phase Control Thyristors** (Stud Version), 80 A



PRIMARY CHARACTERISTICS				
I <sub>T(AV)</sub> 80 A				
V <sub>DRM</sub> /V <sub>RRM</sub>	400 V, 800 V, 1200 V			
$V_{TM}$	1.60 V			
I <sub>GT</sub>	120 mA			
TJ	-40 °C to +125 °C			
Package	TO-94 (TO-209AC)			
Circuit configuration	Single SCR			

#### **FEATURES**





- International standard case TO-94 (TO-209AC)
- · Designed and qualified for industrial level
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

#### **TYPICAL APPLICATIONS**

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
1		80	A		
I <sub>T(AV)</sub>	T <sub>C</sub>	85	°C		
I <sub>T(RMS)</sub>		125			
1	50 Hz	1900	A		
I <sub>TSM</sub>	60 Hz	1990			
121	50 Hz	18	1.42-		
I <sup>2</sup> t	60 Hz	16	- kA <sup>2</sup> s		
V <sub>DRM</sub> /V <sub>RRM</sub>		400 to 1200	V		
t <sub>q</sub>	Typical	110	μs		
TJ		-40 to +125	°C		

#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I <sub>DRM</sub> /I <sub>RRM</sub> MAXIMUM AT T <sub>J</sub> = 125 °C mA				
\(\alpha\)	40	400	500					
VS-80RIA VS-81RIA	80	800	900	15				
VO 0111111	120	1200	1300					



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ABSOLUTE MAXIMUM RATINGS	3					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum average on-state current	<b></b>	180° condu	ction, half sine w	131/0	80	Α
at case temperature	I <sub>T(AV)</sub>	100 Condu	ction, nan sine w	rave	85	°C
Maximum RMS on-state current	I <sub>T(RMS)</sub>	DC at 75 °C	case temperatu	ire	125	
		t = 10 ms	No voltage		1900	A kA <sup>2</sup> s
Maximum peak, one-cycle		t = 8.3 ms	reapplied		1990	
non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>		1600	
		t = 8.3 ms	reapplied	Sinusoidal half wave,	1675	
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	t = 10 ms	No voltage	initial $T_J = T_J$ maximum	18	
		t = 8.3 ms			16	
		t = 10 ms	100 % V <sub>RRM</sub>		12.7	
		t = 8.3 ms	reapplied		11.7	
Maximum I <sup>2</sup> √t for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied		age reapplied	180.5	kA²√s
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x $\pi$ x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum		$I_{T(AV)}$ ), $T_J = T_J$ maximum	0.99	V
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		1.13	]
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x $\pi$ x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum			2.29	mΩ
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		1.84	11152	
Maximum on-state voltage	$V_{TM}$	$I_{pk} = 250 \text{ A}, T_J = 25 ^{\circ}\text{C}, t_p = 10 \text{ ms sine pulse}$		1.60	V	
Maximum holding current	I <sub>H</sub>	T 05 00 and a set 40 V mint of		) \/ registive lead	200	mA
Typical latching current	IL	T <sub>J</sub> = 25 °C, anode supply 12 V resistive load 400		400	] "	

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum non-repetitive rate of rise of turned-on current	dl/dt	$T_J$ = 125 °C, $V_d$ = Rated $V_{DRM}$ , $I_{TM}$ = 2 x dl/dt snubber 0.2 μF, 15 $\Omega$ , gate pulse: 20 V, 65 $\Omega$ , $t_p$ = 6 μs, $t_r$ = 0.5 μs Per JEDEC standard RS-397, 5.2.2.6.	300	A/µs	
Typical delay time	t <sub>d</sub>	Gate pulse: 10 V, 15 $\Omega$ source, $t_p$ = 6 $\mu$ s, $t_r$ = 0.1 $\mu$ s, $V_d$ = Rated $V_{DRM}$ , $I_{TM}$ = 50 Adc, $T_J$ = 25 °C	1		
Typical turn-off time	tq	$I_{TM}$ = 50 A, $T_J$ = $T_J$ maximum, dl/dt = -5 A/μs, $V_R$ = 50 V, dV/dt = 20 V/μs, gate bias: 0 V 25 $\Omega$ , $t_p$ = 500 μs	110	μs  0	

BLOCKING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum critical rate of rise of off-state voltage	dV/dt	T <sub>J</sub> = 125 °C exponential to 67 % rated V <sub>DRM</sub>	500	V/µs		
Maximum peak reverse and off-state leakage current	I <sub>RRM</sub> , I <sub>DRM</sub>	T <sub>J</sub> = 125 °C rated V <sub>DRM</sub> /V <sub>RRM</sub> applied	15	mA		



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TRIGGERING						
PARAMETER	SYMBOL		TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P <sub>GM</sub>	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	12	w	
Maximum average gate power	P <sub>G(AV)</sub>	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	3	VV	
Maximum peak positive gate current	I <sub>GM</sub>			3	Α	
Maximum peak positive gate voltage	+ V <sub>GM</sub>	$T_J = T_J \text{ maximum},$	$t_p \le 5 \text{ ms}$	20	V	
Maximum peak negative gate voltage	- V <sub>GM</sub>			10	v	
	I <sub>GT</sub>	T <sub>J</sub> = - 40 °C	Maximum required gate trigger/ current/voltage are the lowest value which will trigger all units 6 V anode	270	mA	
Maximum DC gate current required to trigger		T <sub>J</sub> = 25 °C		120		
		T <sub>J</sub> = 125 °C		60		
	V <sub>GT</sub>	T <sub>J</sub> = - 40 °C		3.5	V	
Maximum DC gate voltage required to trigger		T <sub>J</sub> = 25 °C	to cathode applied	2.5		
		T <sub>J</sub> = 125 °C		1.5		
DC gate current not to trigger	$I_{GD}$		Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	6	mA	
DC gate voltage not to trigger	$V_{\mathrm{GD}}$	$T_J = T_J$ maximum		0.25	V	

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum operating junction temperature range	TJ		- 40 to 125	°C	
Maximum storage temperature range	T <sub>Stg</sub>		- 40 to 150		
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	0.30	K/W	
Maximum thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, smooth, flat and greased	0.1	r√vv	
W 5 400/		Non-lubricated threads	15.5 (137)	N · m	
Mounting torque, ± 10 %		Lubricated threads	14 (120)	(lbf · in)	
Approximate weight			130	g	
Case style		See dimensions - link at the end of datasheet TO-94 (TO-209		-209AC)	

△R <sub>thJC</sub> CONDUCTION						
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS		
180°	0.042	0.030				
120°	0.050	0.052				
90°	0.064	0.070	$T_J = T_J \text{ maximum}$	K/W		
60°	0.095	0.100				
30°	0.164	0.165				

#### Note

• The table above shows the increment of thermal resistance RthJC when devices operate at different conduction angles than DC

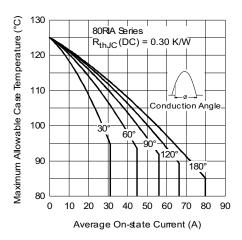


Fig. 1 - Current Ratings Characteristics

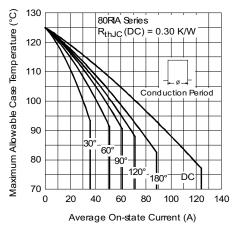


Fig. 2 - Current Ratings Characteristics

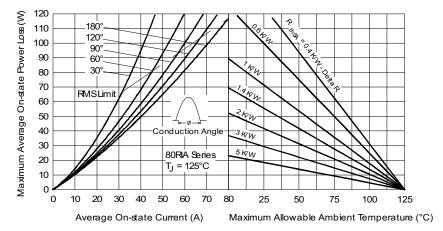


Fig. 3 - On-State Power Loss Characteristics

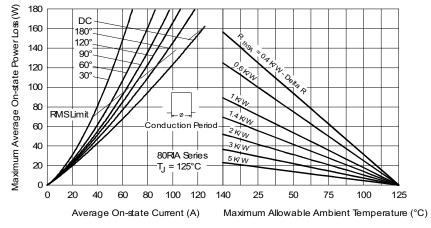


Fig. 4 - On-State Power Loss Characteristics

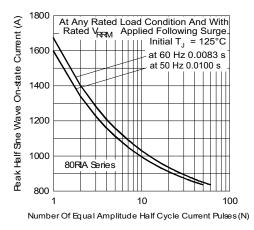


Fig. 5 - Maximum Non-Repetitive Surge Current

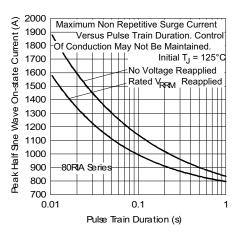


Fig. 6 - Maximum Non-Repetitive Surge Current

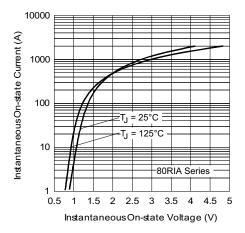


Fig. 7 - On-State Voltage Drop Characteristics

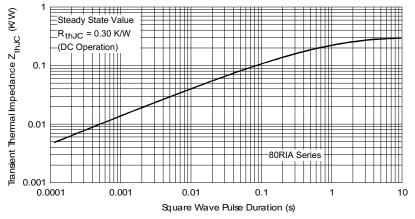


Fig. 8 - Thermal Impedance  $Z_{thJC}$  Characteristics

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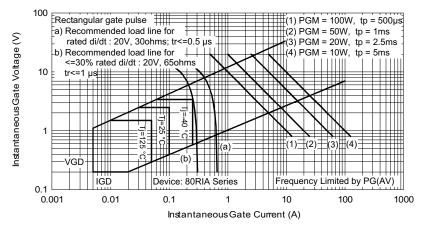
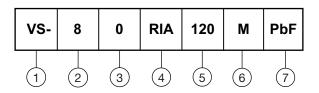


Fig. 9 - Gate Characteristics

#### **ORDERING INFORMATION TABLE**

**Device code** 



- Vishay Semiconductors product
- I<sub>TAV</sub> x 10 A
- 0 = eyelet terminals (gate and auxiliary cathode leads)
  - 1 = fast-on terminals (gate and auxiliary cathode leads)
  - 2 = flag terminals (gate and auxiliary cathode terminals)
- RIA = essential part number
- Voltage code x 100 = V<sub>RRM</sub> (see Voltage Ratings table)
- None = stud base 1/2"-20UNF- 2 A threads
- M = stud base metric threads M12 x 1.75 E 6
- 7 None = standard production
  - PbF = lead (Pb)-free

LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?95362		



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## TO-209AC (TO-94) for 80RIA Series

Ø 23.5 (0.92) MAX.

SW 27

1/2"-20UNF-2A

29.5 (1.16) MAX.

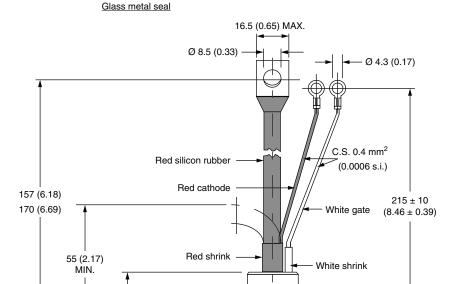
#### **DIMENSIONS** in millimeters (inches)

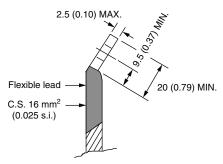
24 (0.94)

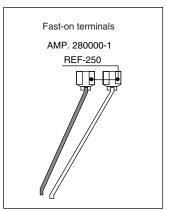
MAX.

10.0 (0.39) MAX.

21 (0.83) MAX.







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T2160N28TOF VT TT251N16KOF-K VS-22RIA100 VS-16RIA40 TD250N16KOF-A VS-ST110S16P0 T930N36TOF VT T2160N24TOF

VT T1190N18TOF VT T1590N28TOF VT 2N1776A T590N14TOF NTE5375 NTE5460 NTE5481 NTE5512 NTE5514 NTE5518

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